

MAC310(A) SERIES

High-reliability discrete products and engineering services since 1977

SILICON BIDIRECTIONAL THYRISTORS

FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak repetitive off-state voltage ⁽¹⁾			
(T _J = -40 to +110°C, $\frac{1}{2}$ sine wave, 50 to 60Hz, gate open)			
MAC310-4, MAC310A-4	V _{DRM}	200	Volts
MAC310-6, MAC310A-6		400	
MAC310-8, MAC310A-8		600	
RMS on-state current (Full cycle sine wave, 50 to 60Hz, T _c = 80°C)	I _{T(RMS)}	10	Amps
Peak non-repetitive surge current			A
(1 cycle, 60Hz, T _J = 110°C)	I _{TSM}	100	Amps
Circuit fusing considerations (t = 8.3ms)	l ² t	40	A ² s
Peak gate current (t \leq 2 μ s)	I _{GM}	±2	Amps
Peak gate voltage (t $\leq 2\mu$ s)	V _{GM}	±10	Volts
Peak gate power (t $\leq 2\mu$ s)	P _{GM}	20	Watts
Average gate power ($T_c = 80^{\circ}C$, $t \le 8.3ms$)	P _{G(AV)}	0.5	Watts
Operating junction temperature range	TJ	-40 to +110	°C
Storage temperature range	T _{stg}	-40 to +150	°C
Mounting torque		8	In. lb.

Note 1: VDRM for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Maximum	Unit
Thermal resistance, junction to case	R _{ejc}	2.2	°C/W
Thermal resistance, junction to ambient	R _{eja}	60	°C/W

ELECTRICAL CHARACTERISTICS (T_c = 25°C and either polarity of MT2 to MT1 voltage unless otherwise noted)

Characteristic	Symbol	Min	Тур.	Max	Unit
Peak blocking current					
(V_D = Rated V_{DRM} , gate open, T_J = 25°C)	I _{DRM}	-	-	10	mA
(V _D = Rated V _{DRM} , gate open, T _J = 110°C)		-	-	2	mA
Peak on-state voltage					Valta
(I_{TM} = 14A peak, pulse width \leq 2ms, duty cycle \leq 2%.)	V _{TM}	-	-	2.0	Volts
Gate trigger current (continuous dc)					
$(V_{D} = 12V, R_{L} = 100\Omega)$					
MT2(+),G(+); MT2(+),G(-); MT2(-),G(-)	I _{GT}	-	-	5	mA
MT2(-),G(+) "A" suffix only		-	-	10	
Gate trigger voltage (continuous dc)					
$(V_D = 12V, R_L = 100\Omega)$					
MT2(+),G(+); MT2(+),G(-); MT2(-),G(-)	V	-	-	2.0	Volts
MT2(-),G(+) "A" suffix only	V _{GT}	-	-	2.5	VOILS
(V_D = Rated V_{DRM} , R_L = 10k Ω , T_C = 110°C)					
All Types		0.2	-	-	



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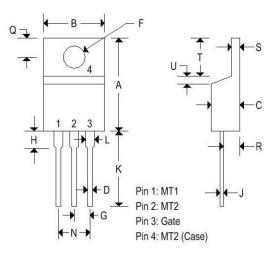
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Holding current ($V_D = 12V$, $I_{TM} = 200$ mA, gate open)	I _H	-	-	15	mA
Gate controlled turn-on time (V_D = Rated V_{DRM} , I_{TM} = 14A, I_G = 30mA)	t _{gt}	-	1.5	-	μs
Critical rate of rise of off-state voltage (V_D = Rated V_{DRM} , exponential waveform, T_C = 110°C)	dv/dt	-	25	-	V/µs
Critical rate of rise of commutation voltage (V_D = Rated V_{DRM} , I_{TM} = 14A peak, commutating di/dt = 5A/ms, gate unenergized, T_C = 80°C)	dv/dt(c)	-	5	-	V/µs

MECHANICAL CHARACTERISTICS

Case	ТО-220АВ
Marking	Alpha-numeric
Pin out	See below



	TO-220AB			
	Inc	Inches		neters
	Min	Max	Min	Max
Α	0.575	0.620	14.600	15.750
В	0.380	0.405	9.650	10.290
С	0.160	0.190	4.060	4.820
D	0.025	0.035	0.640	0.890
F	0.142	0.147	3.610	3.730
G	0.095	0.105	2.410	2.670
Н	0.110	0.155	2.790	3.930
J	0.014	0.022	0.360	0.560
К	0.500	0.562	12.700	14.270
L	0.045	0.055	1.140	1.390
Ν	0.190	0.210	4.830	5.330
Q	0.100	0.120	2.540	3.040
R	0.080	0.110	2.040	2.790
S	0.045	0.055	1.140	1.390
T	0.235	0.255	5.970	6.480
U	1	0.050	40	1.270
۷	0.045		1.140	
Ζ	- 20	0.080		2.030



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T_C, CASE TEMPERATURE (°C)

120

110

100

90

80

0

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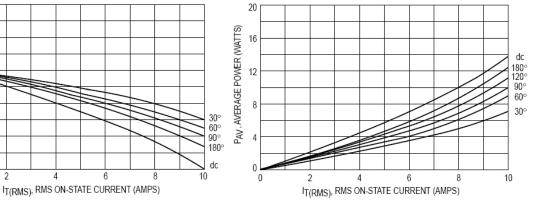


Figure 1. RMS Current Derating

Figure 2. On-State Power Dissipation